

Photoconductivity of Few-Layer MoTe₂

T. J. Octon^{1*}, K. Nagareddy¹, M. F. Craciun¹ and C. D. Wright¹

¹Department of Engineering, University of Exeter, Exeter, EX4 4QF, UK

*corresponding author: tjo201@ex.ac.uk

Abstract – A photoconductivity study of few-layer MoTe₂ in a field effect transistor (FET) configuration was performed to find the photoresponsivity and photocurrent response of the material. The mechanisms for MoTe₂ with no applied gate voltage were found to be dominated by the photovoltaic effect, showing its potential for use in solar cells. Due to the band gap of MoTe₂ being 1.1 eV, MoTe₂ is a suitable photodetector for optical wavelengths and potentially the near infrared.

Transition metal dichalcogenides (TMDCs) have been the subject of intense research due to their impressive optoelectronic properties, showing lower noise photodetection than silicon photodiodes,¹ and high photoresponsivities.²⁻⁴ MoTe₂ has a band gap of ~1 – 1.2 eV from bulk to the monolayer thickness, transitioning to a direct gap at monolayer thickness.⁵ In our work, we measure the optoelectronic properties of this overlooked TMDC as a transistor and photodetector. We fabricated the FETs using electron beam lithography and thermal evaporation of a Cr/Au layer. We characterized the layer thickness using three techniques, optical contrast, atomic force microscopy and Raman spectroscopy. Measurements were taken using a DC measurement setup and a 685 nm laser and 50x objective lens. So far our results show signs that MoTe₂ is suitable for both fast and responsive photodetection.

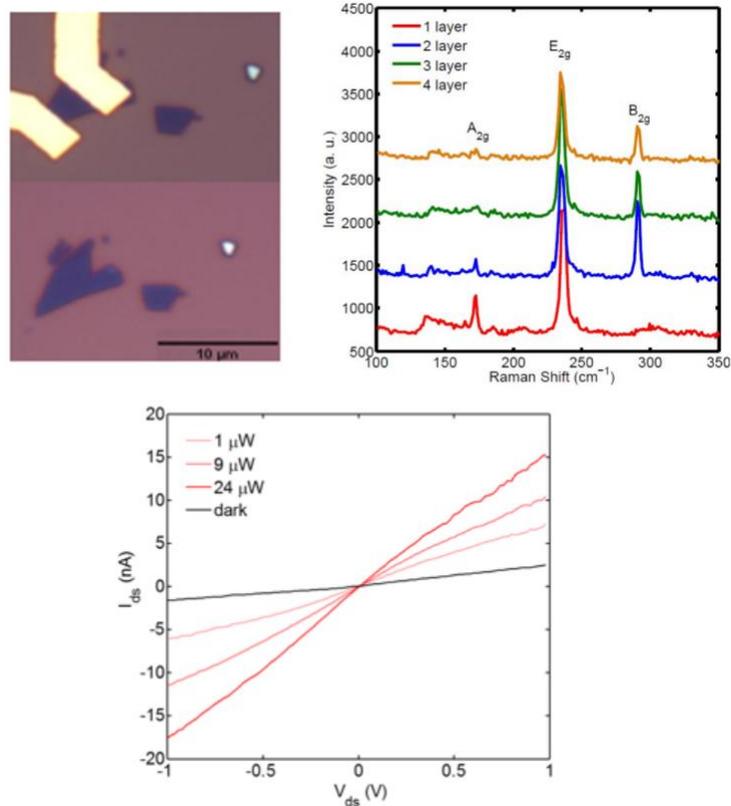


Fig. 1(a) we show an optical image of a 4 layer MoTe₂ flake before and after our fabrication. In Fig. 1(b) the Raman spectra of MoTe₂ is included up to four layers, the ratio of areas underneath the E¹_{2g} and B¹_{2g} peaks provide information for the layer thickness. Fig. 1(c) An output characteristic of few layer MoTe₂ with a 685 nm laser up to powers of 24 μW.

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